

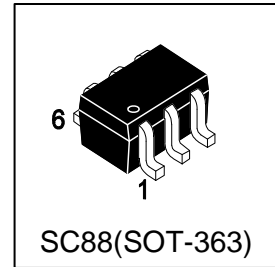
# LBC847BDW1T1G

## S-LBC847BDW1T1G

NPN Dual General Purpose Transistors

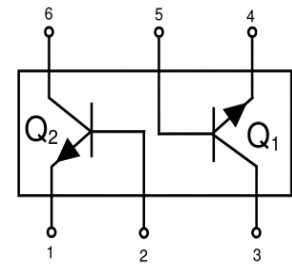
### 1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.



### 2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBC847BDW1T1G	1F	3000/Tape&Reel
LBC847BDW1T3G	1F	10000/Tape&Reel



### 3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector–Emitter Voltage	V <sub>CEO</sub>	45	V
Collector–Base Voltage	V <sub>CBO</sub>	50	V
Emitter–Base Voltage	V <sub>EB0</sub>	6	V
Collector Current(Continuous)	I <sub>C</sub>	100	mA

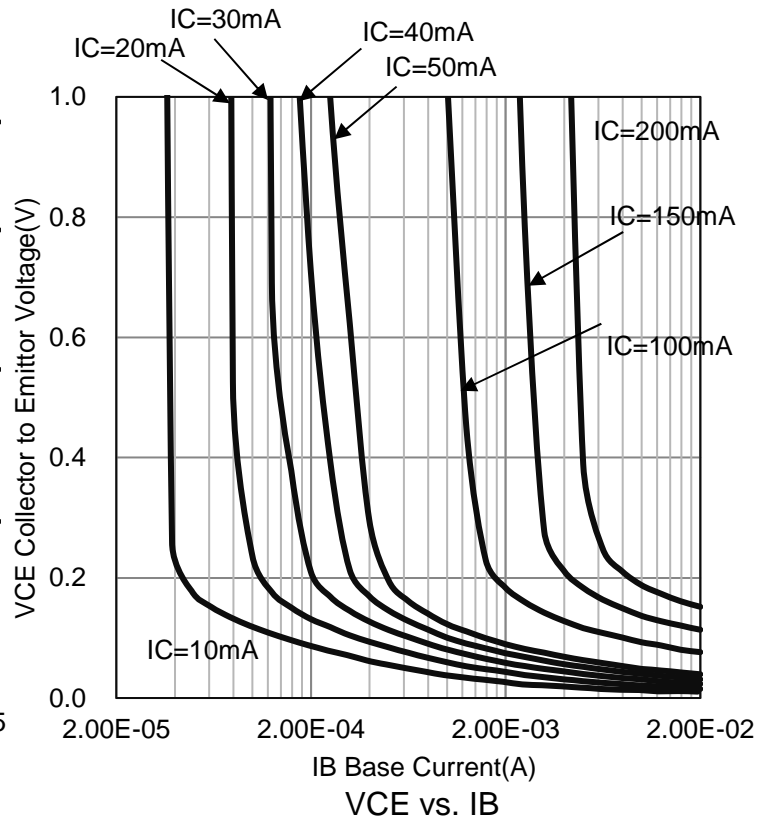
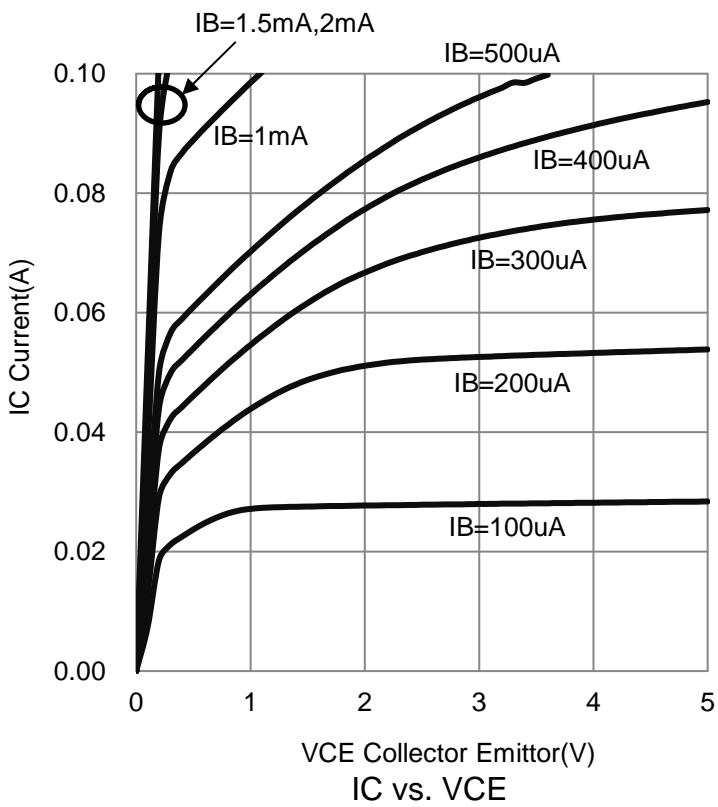
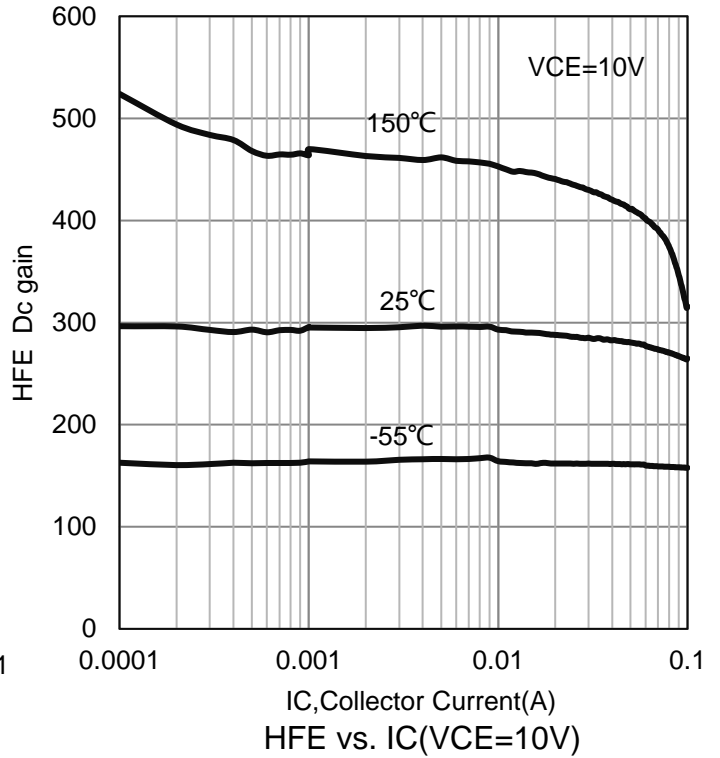
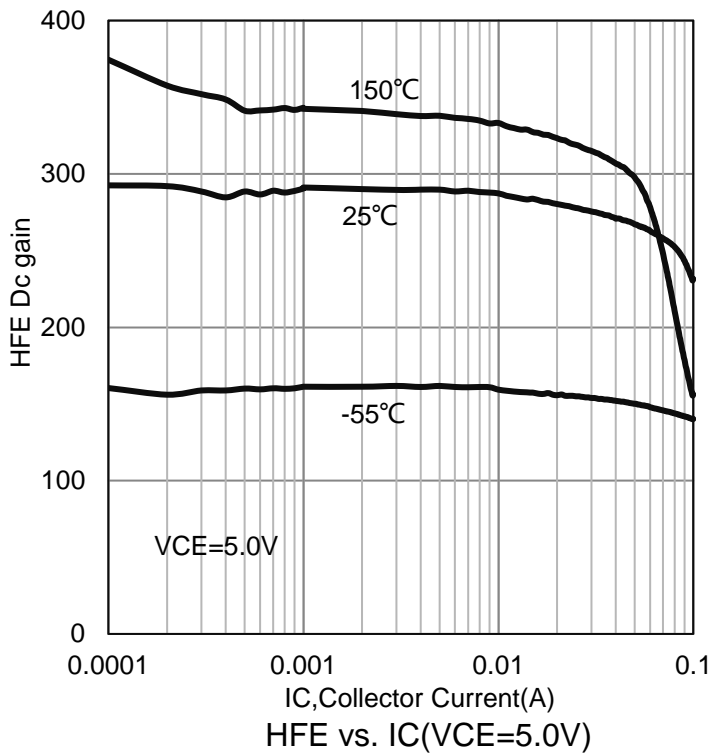
### 4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation		380	mW
FR– 5 Board, (1) T A = 25°C	PD	250	mW
Derate above 25°C		3	mW/°C
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	328	°C/W
Junction and Storage Temperature	T <sub>J</sub> ,T <sub>stg</sub>	-55 ~ +150	°C

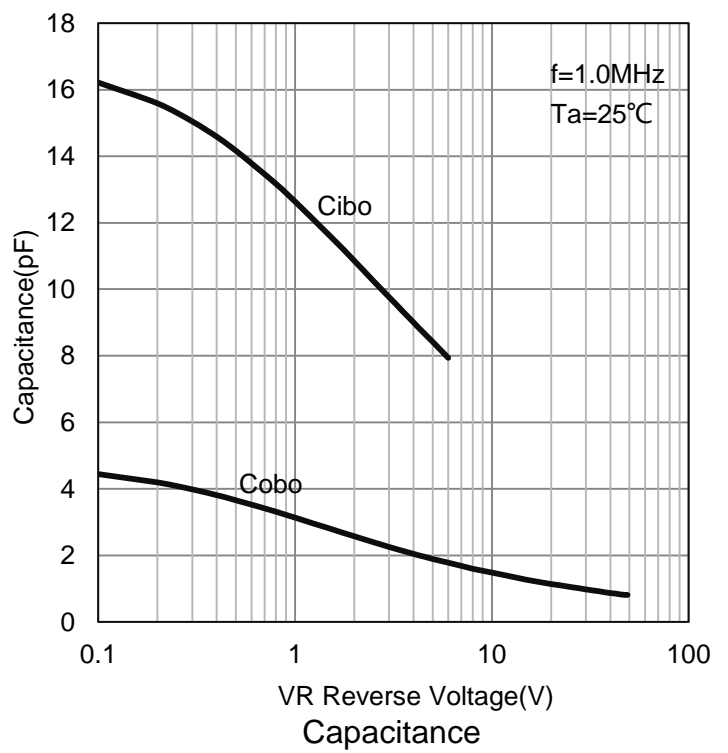
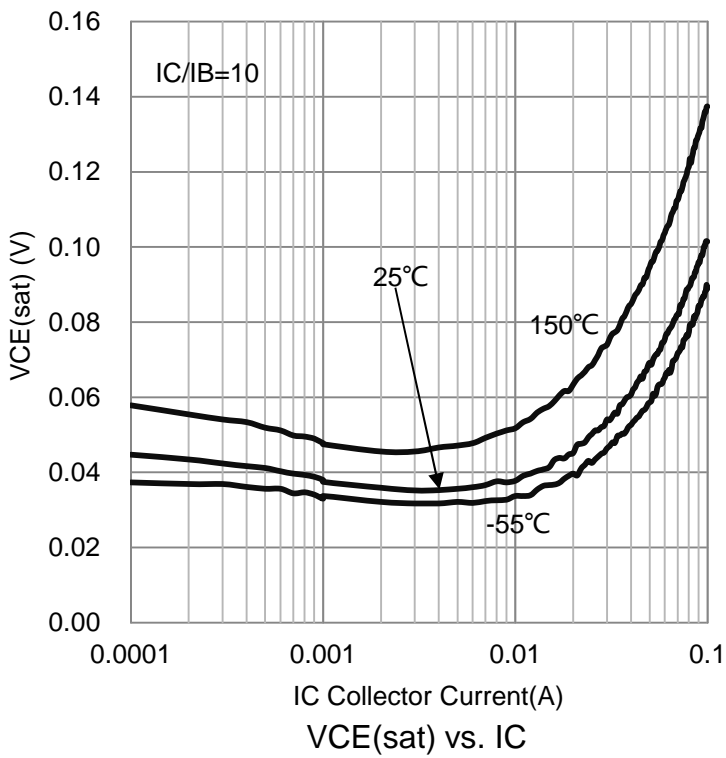
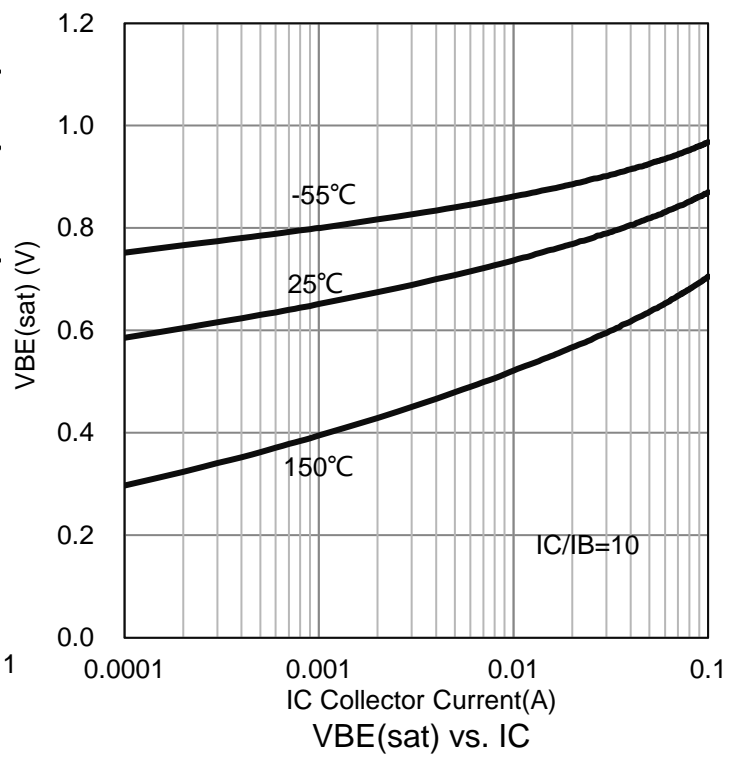
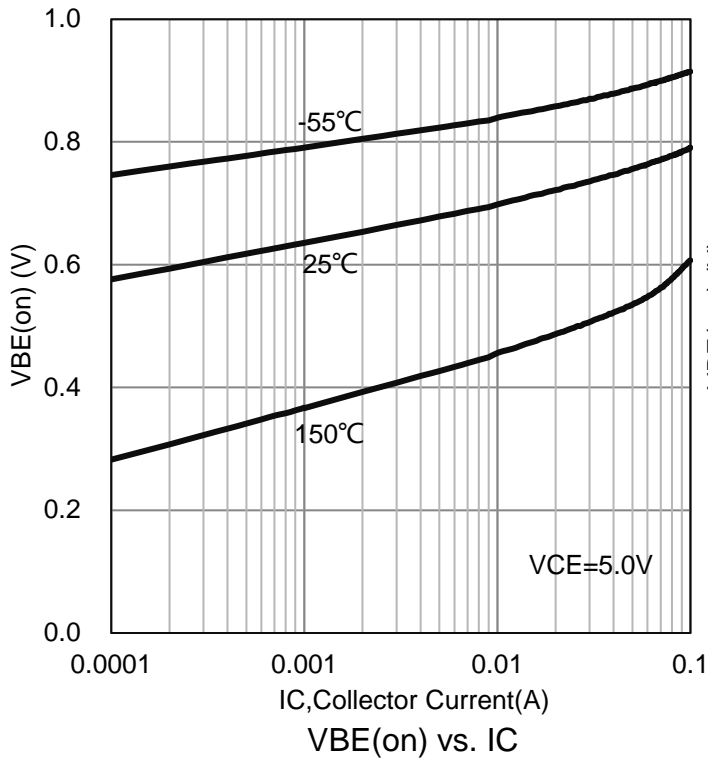
**5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)**

Characteristic	Symbol	Min.	Typ.	Max.	Unit
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Breakdown Voltage (IC = 10 mA)	V(BR)CEO	45	-	-	V
Collector–Emitter Breakdown Voltage (IC = 10 μA, VEB = 0)	V(BR)CES	50	-	-	V
Collector–Base Breakdown Voltage (IC = 10 μA)	V(BR)CBO	50	-	-	V
Emitter–Base Breakdown Voltage (IE = 1.0 μA)	V(BR)EBO	6	-	-	V
Collector Cutoff Current (VCB = 30 V) (VCB = 30 V, TA = 150°C)	ICBO	- -	- -	15 5	nA μA
<b>ON CHARACTERISTICS</b>					
DC Current Gain (IC = 2.0 mA, VCE = 5.0 V)	hFE	200	290	450	
Collector–Emitter Saturation Voltage (IC = 10 mA, IB = 0.5 mA) (IC = 100 mA, IB = 5.0 mA)	VCE(sat)	- -	- -	0.25 0.6	V
Base–Emitter Saturation Voltage (IC = 10 mA, IB = 0.5 mA) (IC = 100 mA, IB = 5.0 mA)	VBE(sat)	- -	0.7 0.9	- -	V
Base–Emitter Voltage (IC = 2.0 mA, VCE = 5.0 V) (IC = 10 mA, VCE = 5.0 V)	VBE(on)	580 -	660 -	700 770	mV
<b>SMALL–SIGNAL CHARACTERISTICS</b>					
Current–Gain — Bandwidth Product (IC = 10 mA, VCE = 5.0 Vdc, f = 100 MHz)	fT	100	-	-	MHz
Output Capacitance (VCB = 10 V, f = 1.0 MHz)	Cobo	-	-	4.5	pF
Noise Figure(IC = 0.2 mA, VCE = 5.0 V, RS = 2.0 kΩ, f = 1.0 KHz, BW = 200 Hz)	NF	-	-	10	dB

### 6. ELECTRICAL CHARACTERISTICS CURVES



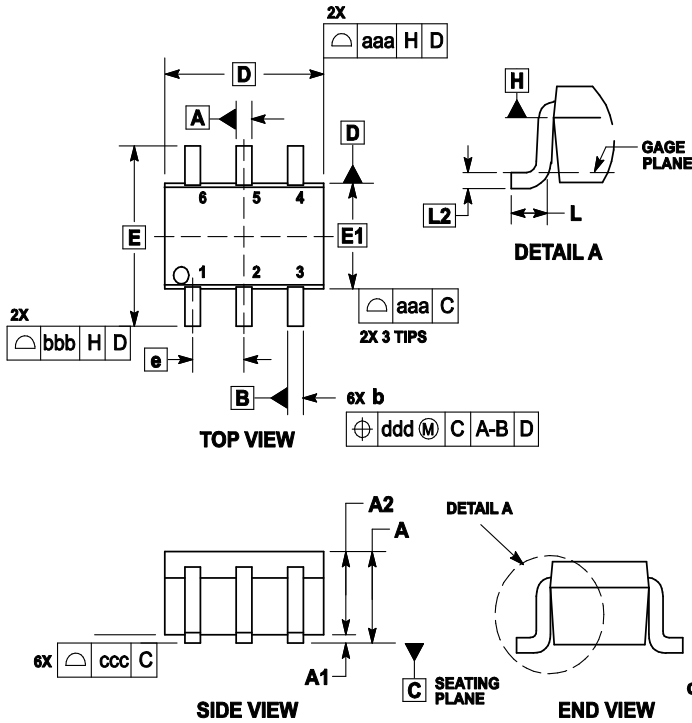
### 6. ELECTRICAL CHARACTERISTICS CURVES (Con.)



### 7. OUTLINE AND DIMENSIONS

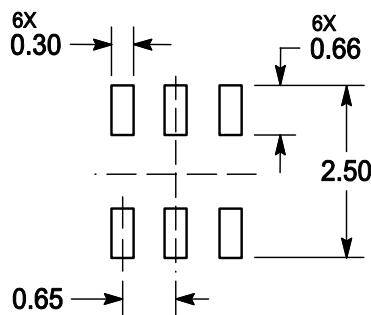
Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.01
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.07	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.01		
bbb	0.30			0.01		
ccc	0.10			0.00		
ddd	0.10			0.00		

### 8. SOLDERING FOOTPRINT



单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)